

## **isc** Silicon NPN Power Transistor

# 2N4114

### DESCRIPTION

- Excellent Safe Operating Area
- Low Collector-Emitter Saturation Voltage
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.

### **APPLICATIONS**

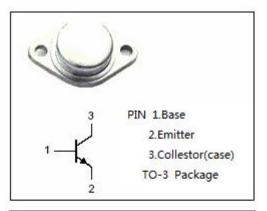
Designed for general-purpose switching and amplifier applications

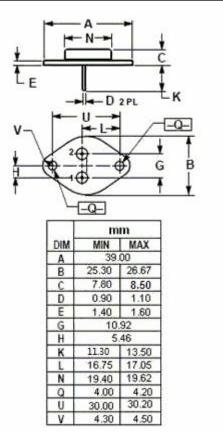
### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL           | PARAMETER                           | VALUE    | UNIT |
|------------------|-------------------------------------|----------|------|
| V <sub>сво</sub> | Collector-Base Voltage              | 120      | V    |
| V <sub>CEO</sub> | Collector-Emitter Voltage           | 80       | V    |
| V <sub>EBO</sub> | Emitter-Base Voltage                | 8        | V    |
| lc               | Collector Current-Continuous        | 5        | А    |
| Pc               | Collector Power Dissipation@Tc=25°C | 30       | W    |
| TJ               | Operating Temperature Range         | -65~+165 | °C   |
| T <sub>stg</sub> | Storage Junction Temperature Range  | -65~+165 | °C   |

### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                            | MAX  | UNIT |
|---------------------|--------------------------------------|------|------|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case | 4.67 | °C/W |







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### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

| SYMBOL           | PARAMETER                            | CONDITIONS   | MIN | МАХ | UNIT |
|------------------|--------------------------------------|--|-----|-----|------|
| VCEO(SUS)        | Collector-Emitter Sustaining Voltage | I <sub>C</sub> =30mA ; I <sub>в</sub> =0               | 80  |     | V    |
| I <sub>CEO</sub> | Collector Cutoff Current             | V <sub>CE</sub> = 60V; I <sub>B</sub> =0               |     | 0.1 | mA   |
| I <sub>EBO</sub> | Emitter Cutoff Current               | V <sub>EB</sub> = 8.0V; I <sub>C</sub> =0              |     | 1   | mA   |
| hfe              | DC Current Gain                      | Ic= 2A ; Vc= 5V  | 100 | 200 |      |
| f <sub>T</sub>   | Current Gain-Bandwidth Product       | I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 10V;f=1.0MHz | 60  |     | MHz  |

#### NOTICE:

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